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(71) Applicant (for all designated States except US): **YISSUM RESEARCH DEVELOPMENT COMPANY OF THE HEBREW UNIVERSITY OF JERUSALEM [IL/IL]**;
Hi Tech Park, Edmond Safra Campus, Givat Ram, 91390 Jerusalem (IL).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **BANIN, Uri [IL/IL]**;

37 Yasmin Street, 90805 Mevasseret Zion (IL). **MOKARI, Taleb [IL/IL]**; Givat Ram 4/208, P.O.B. 39183, 91391 Jerusalem (IL).

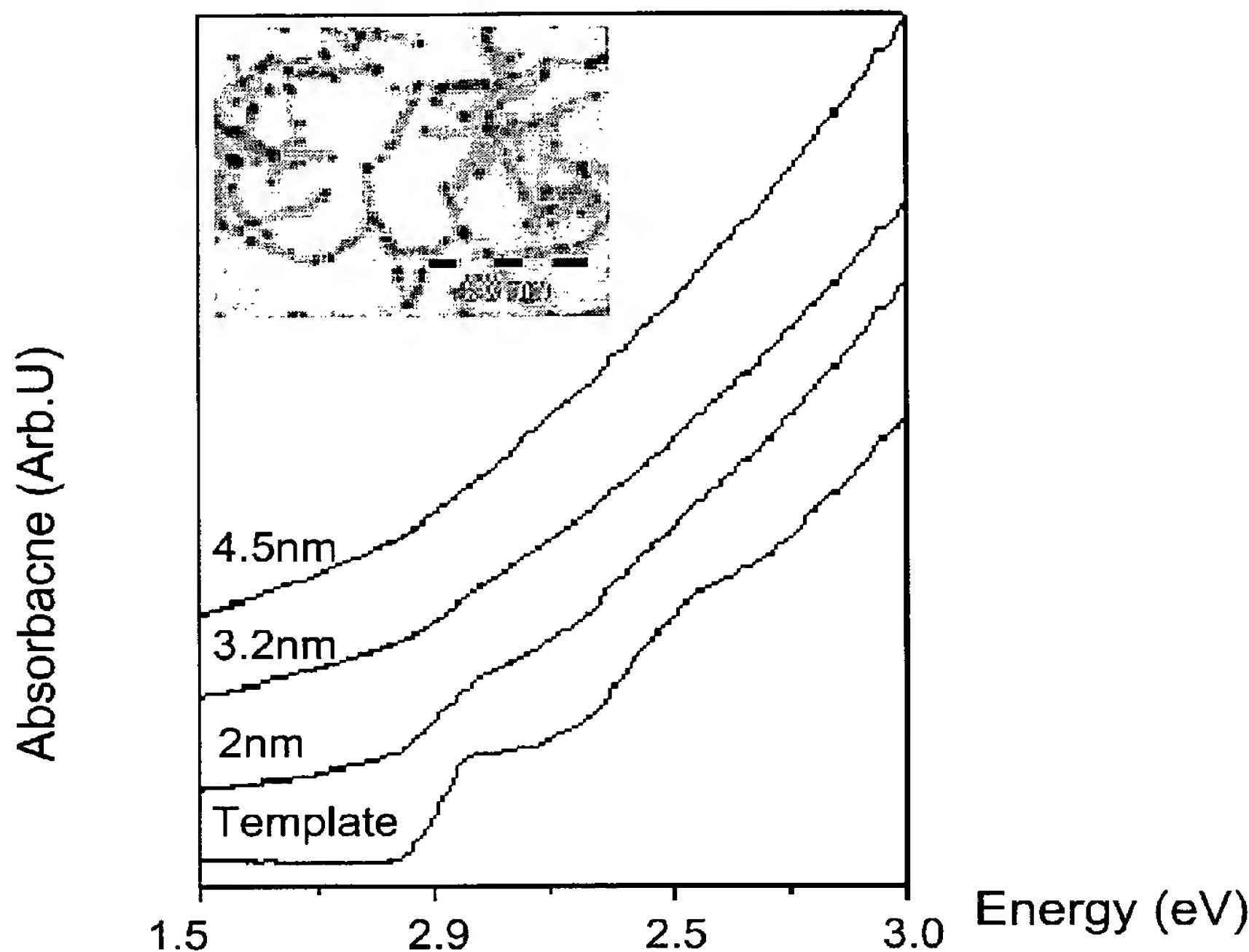
(74) Agent: **REINHOLD COHN AND PARTNERS**; P.O.Box 4060, 61040 Tel Aviv (IL).

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(54) Title: NOVEL NANOSTRUCTURES AND METHOD FOR SELECTIVE PREPARATION



(57) Abstract: The present invention provides novel nanostructure composed of at least one elongated structure element, an elongated structure element of said nanostructure bearing a different zone made of metal, metal alloy, conductive polymer or semiconductor and selectively grown onto at least one of the end portions of the elongated structure element. The present invention further provides a selective method for forming in a liquid medium, such nanostructures.



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